Kei May Lau

List of Publications by Year
in descending order

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240 papers	5,384 citations	71061 41 h-index	128225 60 g-index
240 all docs	240 docs citations	240 times ranked	3472 citing authors

#	Article	IF	Citations
1	Enhancing ON- and OFF-State Performance of Quasi-Vertical GaN Trench MOSFETs on Sapphire With Reduced Interface Charges and a Thick Bottom Dielectric. IEEE Electron Device Letters, 2022, 43, 346-349.	2.2	10
2	Gain-switching of 1.55 Âµm InP-based Qdash lasers grown on Si. AIP Advances, 2022, 12, 025315.	0.6	1
3	III-V Micro/Nano-lasers and photodetectors in the Telecom Band Grown on SOI. , 2022, , .		0
4	Full-color micro-display by heterogeneous integration of InGaN blue/green dual-wavelength and AlGaInP red LEDs. Optics Express, 2022, 30, 23499.	1.7	9
5	Telecom InGaAs/InP Quantum Well Lasers Laterally Grown on Silicon-on-Insulator. Journal of Lightwave Technology, 2022, 40, 5631-5635.	2.7	10
6	Vertical GaN trench MOSFETs with step-graded channel doping. Applied Physics Letters, 2022, 120, .	1.5	1
7	Dynamic Characteristics of GaN MISHEMT With 5-nm In-Situ SiN_x Dielectric Layer. IEEE Journal of the Electron Devices Society, 2022, 10, 540-546.	1.2	3
8	Monolithic fullâ€color microdisplay using patterned quantum dot photoresist on dualâ€wavelength LED epilayers. Journal of the Society for Information Display, 2021, 29, 157-165.	0.8	19
9	Active matrix monolithic microâ€LED fullâ€color microâ€display. Journal of the Society for Information Display, 2021, 29, 47-56.	0.8	47
10	40 G III-V photodetectors on a monolithic InP/SOI platform. , 2021, , .		1
11	1300 V Normally-OFF p-GaN Gate HEMTs on Si With High ON-State Drain Current. IEEE Transactions on Electron Devices, 2021, 68, 653-657.	1.6	39
12	Selectively Grown III-V Lasers for Integrated Si-Photonics. Journal of Lightwave Technology, 2021, 39, 940-948.	2.7	25
13	Ambipolar Photocarrier Doping and Transport in Monolayer WSâ„‚ by Forming a Graphene/WSâ„‚/Quantum Dots Heterostructure. IEEE Electron Device Letters, 2021, 42, 371-374.	2.2	2
14	848 ppi high-brightness active-matrix micro-LED micro-display using GaN-on-Si epi-wafers towards mass production. Optics Express, 2021, 29, 10580.	1.7	34
15	GaSb-based laser diodes grown on MOCVD GaAs-on-Si templates. Optics Express, 2021, 29, 11268.	1.7	9
16	Monolithic integration of ultraviolet light emitting diodes and photodetectors on a p-GaN/AlGaN/GaN/Si platform. Optics Express, 2021, 29, 8358.	1.7	24
17	Optical gain and absorption of 1.55â€‰Î¼m InAs quantum dash lasers on silicon substrate. Applied Physics Letters, 2021, 118, .	1.5	5
18	Telecom InP-based quantum dash photodetectors grown on Si. Applied Physics Letters, 2021, 118, .	1.5	11

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19	Controlled single-mode emission in quantum dot micro-lasers. Optics Express, 2021, 29, 13193.	1.7	2
20	C and L band room-temperature continuous-wave InP-based microdisk lasers grown on silicon. Optics Letters, 2021, 46, 2836.	1.7	10
21	Monolithic Thin Film Red LED Active-Matrix Micro-Display by Flip-Chip Technology. IEEE Photonics Technology Letters, 2021, 33, 603-606.	1.3	10
22	Effects of p-GaN Body Doping Concentration on the ON-State Performance of Vertical GaN Trench MOSFETs. IEEE Electron Device Letters, 2021, 42, 970-973.	2.2	7
23	Red-emitting InP quantum dot micro-disk lasers epitaxially grown on (001) silicon. Optics Letters, 2021, 46, 4514.	1.7	6
24	High-performance III-V photodetectors on a monolithic InP/SOI platform. Optica, 2021, 8, 1204.	4.8	33
25	A monolithic InP/SOI platform for integrated photonics. Light: Science and Applications, 2021, 10, 200.	7.7	47
26	Thin-barrier heterostructures enabled normally-OFF GaN high electron mobility transistors. Semiconductor Science and Technology, 2021, 36, 034001.	1.0	8
27	Lasers on an InP/SOI platform with dislocation-free in-plane InP sub-micron bars and membranes. , 2021, , .		0
28	Gain switching of 1.55 Î¼m QDash Lasers directly grown on Silicon. , 2021, , .		0
29	Trap Characterization of InGaN/GaN Blue Light Emitting Diode Grown on Si Substrate. , 2021, , .		0
30	Ultra-low threshold optically pumped single mode InP micro-lasers grown on SOI. , 2021, , .		0
31	Vertical Î²â€Ga₂O₃ Schottky Barrier Diodes with Enhanced Breakdown Voltage and High Switching Performance. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900497.	0.8	34
32	Low Dark Current High Gain InAs Quantum Dot Avalanche Photodiodes Monolithically Grown on Si. ACS Photonics, 2020, 7, 528-533.	3.2	49
33	23â€5: Lateâ€News Paper: Highâ€Resolution Monolithic Microâ€LED Fullâ€color Microâ€display. Digest of Technical Papers SID International Symposium, 2020, 51, 339-342.	0.1	6
34	Selective lateral photoelectrochemical wet etching of InGaN nanorods. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, 060602.	0.6	2
35	IIIâ€“V lasers selectively grown on (001) silicon. Journal of Applied Physics, 2020, 128, .	1.1	28
36	Ultra-low threshold green InGaN quantum dot microdisk lasers grown on silicon. Applied Physics Letters, 2020, 117, .	1.5	7

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37	Leakage Current Reduction in Î²-Ga₂O₃ Schottky Barrier Diodes by CF₄ Plasma Treatment. IEEE Electron Device Letters, 2020, 41, 1312-1315.	2.2	19
38	InAs nano-ridges and thin films grown on (001) silicon substrates. Journal of Applied Physics, 2020, 128, .	1.1	9
39	High gain and high ultraviolet/visible rejection ratio photodetectors using p-GaN/AlGaN/GaN heterostructures grown on Si. Applied Physics Letters, 2020, 117, .	1.5	39
40	Forward Conduction Instability of Quasi-Vertical GaN p-i-n Diodes on Si Substrates. IEEE Transactions on Electron Devices, 2020, 67, 3992-3998.	1.6	7
41	Micrometer-scale InP selectively grown on SOI for fully integrated Si-photonics. Applied Physics Letters, 2020, 117, .	1.5	20
42	Comparative Study on Dynamic Characteristics of GaN HEMT at 300K and 150K. IEEE Journal of the Electron Devices Society, 2020, 8, 850-856.	1.2	6
43	InP-based Lasers Grown on 220 nm SOI by Lateral/vertical Aspect Ratio Trapping. , 2020, , .		0
44	IIIâ€“V micro- and nano-lasers deposited on amorphous SiO2. Applied Physics Letters, 2020, 116, .	1.5	5
45	Multi-heterojunction InAs/GaSb nano-ridges directly grown on (001) Si. Nanotechnology, 2020, 31, 345707.	1.3	8
46	GaN Single Nanowire pâ€“iâ€“n Diode for High-Temperature Operations. ACS Applied Electronic Materials, 2020, 2, 719-724.	2.0	7
47	Comparison of the AlN and GaN crystalline quality on 2-inch silicon substrate via two growth methods. Journal of Crystal Growth, 2020, 535, 125545.	0.7	13
48	1-kV Sputtered p-NiO/n-Ga₂O₃ Heterojunction Diodes With an Ultra-Low Leakage Current Below $1~mu$ A/cm². IEEE Electron Device Letters, 2020, 41, 449-452.	2.2	129
49	Low Threshold Quantum Dot Lasers Directly Grown on Unpatterned Quasi-Nominal (001) Si. IEEE Journal of Selected Topics in Quantum Electronics, 2020, 26, 1-9.	1.9	29
50	MOCVD growth of InP-based 1.3â€‰ Î¼ m quantum dash lasers on (001) Si. Applied Physics Letters, 2020, 116, .	1.5	8
51	1.55â€…Âµm electrically pumped continuous wave lasing of quantum dash lasers grown on silicon. Optics Express, 2020, 28, 18172.	1.7	40
52	Comparison of static and dynamic characteristics of 1550â€…nm quantum dash and quantum well lasers. Optics Express, 2020, 28, 26823.	1.7	7
53	Bufferless IIIâ€“V photodetectors directly grown on (001) silicon-on-insulators. Optics Letters, 2020, 45, 1754.	1.7	18
54	Bufferless 1.5â€‰â€‰Âµm III-V lasers grown on Si-photonics 220â€‰â€‰nm silicon-on-insulator platforms. Optica, 2020, 7, 148.	4.8	53

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55	Low-efficiency-droop InGaN quantum dot light-emitting diodes operating in the â€œgreen gapâ€• Photonics Research, 2020, 8, 750.	3.4	21
56	Comparison of growth structures for continuous-wave electrically pumped 1.55â€‰Î¼m quantum dash lasers grown on (001) Si. Photonics Research, 2020, 8, 1888.	3.4	16
57	III-V micro- and nano-lasers grown on silicon emitting in the telecom band. , 2020, , .		0
58	InGaN quantum dots with short exciton lifetimes grown on polar c-plane by metal-organic chemical vapor deposition. Materials Research Express, 2020, 7, 115903.	0.8	1
59	III-V Superlattices on InP/Si Metamorphic Buffer Layers for Î» â‰ˆ4.8â€‰Î¼m Quantum Cascade Lasers. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800493.	0.8	4
60	1.55-Î¼m Lasers Epitaxially Grown on Silicon. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-11.	1.9	35
61	Low-Threshold Epitaxially Grown 1.3-Î¼m InAs Quantum Dot Lasers on Patterned (001) Si. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-7.	1.9	23
62	High Responsivity and Low Dark Current Ultraviolet Photodetectors Using p-GaN/AlGaN/GaN Heterostructure. , 2019, , .		1
63	High-Voltage p-GaN HEMTs With OFF-State Blocking Capability After Gate Breakdown. IEEE Electron Device Letters, 2019, 40, 530-533.	2.2	50
64	4â€‰: Invited Paper: Microâ€‰LED displays: can the monolithic approach produce fullâ€‰color?. Digest of Technical Papers SID International Symposium, 2019, 50, 20-21.	0.1	1
65	Exciton aggregation induced photoluminescence enhancement of monolayer WS2. Applied Physics Letters, 2019, 114, .	1.5	11
66	Selective lateral epitaxy of dislocation-free InP on silicon-on-insulator. Applied Physics Letters, 2019, 114, 192105.	1.5	26
67	Self-Powered Fast-Response X-Ray Detectors Based on Vertical GaN p-n Diodes. IEEE Electron Device Letters, 2019, 40, 1044-1047.	2.2	22
68	Active Matrix Monolithic LED Micro-Display Using GaN-on-Si Epilayers. IEEE Photonics Technology Letters, 2019, 31, 865-868.	1.3	66
69	Defect Characterization of InAs/InGaAs Quantum Dot p-i-n Photodetector Grown on GaAs-on-V-Grooved-Si Substrate. ACS Photonics, 2019, 6, 1100-1105.	3.2	37
70	Growth of IIIâ€“V semiconductors and lasers on silicon substrates by MOCVD. Semiconductors and Semimetals, 2019, , 229-282.	0.4	6
71	Mechanism of Wavelength Tuning over 200 nm Range from InP/InGaAs Nano-Lasers Grown on SOI. , 2019, , .		0
72	Monolithic Î¼-LED Full-Color Micro-Displays. , 2019, , .		0

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73	Monolithic Growth of InAs Quantum Dots Lasers on (001) Silicon Emitting at 1.55 Î¼m. , 2019, , .		0
74	Telecom III-V Nano-Lasers with Distributed Bragg Reflectors Grown on (001) Silicon-on-Insulators. , 2019, , .		0
75	Characteristics of 1.3Î¼m Electrically Pumped InAs/AlGaInAs Quantum Dot Lasers on (001) Silicon. , 2019, , .		0
76	Electrically injected 164Âµm emitting In₀₆₅Ga₀₃₅As 3-QW laser diodes grown on mismatched substrates by MOVPE. Optics Express, 2019, 27, 33205.	1.7	6
77	Telecom InP/InGaAs nanolaser array directly grown on (001) silicon-on-insulator. Optics Letters, 2019, 44, 767.	1.7	45
78	Electrically pumped 15â€‰â€‰Î¼m InP-based quantum dot microring lasers directly grown on (001) Si. Optics Letters, 2019, 44, 4566.	1.7	25
79	Broadband telecom emission from InP/InGaAs nano-ridge lasers on silicon-on-insulator substrate. OSA Continuum, 2019, 2, 3037.	1.8	4
80	Room temperature IIIâ€“V nanolasers with distributed Bragg reflectors epitaxially grown on (001) silicon-on-insulators. Photonics Research, 2019, 7, 1081.	3.4	14
81	Triple reduction of threshold current for 1.3 Î¼m InAs quantum dot lasers on patterned, on-axis (001) Si. , 2019, , .		0
82	III-V Lasers Emitting at 1.3 to 1.5 Âµm grown on (001) silicon by MOCVD (invited). , 2019, , .		0
83	An Auto-Zero-Voltage-Switching Quasi-Resonant LED Driver With GaN FETs and Fully Integrated LED Shunt Protectors. IEEE Journal of Solid-State Circuits, 2018, 53, 913-923.	3.5	13
84	Voltage-Controlled GaN HEMT-LED Devices as Fast-Switching and Dimmable Light Emitters. IEEE Electron Device Letters, 2018, 39, 224-227.	2.2	42
85	Heterointerface study of InAs/GaSb nanoridge heterostructures grown by metal organic chemical vapor deposition on V-grooved Si (0â€¯0â€¯1) substrates. Journal of Crystal Growth, 2018, 484, 12-16.	0.7	1
86	A Novel 700 V Monolithically Integrated Si-GaN Cascoded Field Effect Transistor. IEEE Electron Device Letters, 2018, 39, 394-396.	2.2	13
87	Enhancement-Mode GaN MOS-HEMTs With Recess-Free Barrier Engineering and High- ${k}$ ZrO2 Gate Dielectric. IEEE Electron Device Letters, 2018, 39, 405-408.	2.2	50
88	InGaAs/InP quantum wires grown on silicon with adjustable emission wavelength at telecom bands. Nanotechnology, 2018, 29, 225601.	1.3	27
89	InAs Quantum Dots Lasers Directly Grown on Silicon Emitting at Telecom Wavelengths. , 2018, , .		0
90	Integration of III-V Compounds on Silicon by Hetero-epitaxy. , 2018, , .		1

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91	1.5 Î¼m quantum-dot diode lasers directly grown on CMOS-standard (001) silicon. Applied Physics Letters, 2018, 113, .	1.5	50
92	31.3: Low Optical Crosstalk Microâ€LED Microâ€Display with Semiâ€Sphere Microâ€Lens for Light Collimation. Digest of Technical Papers SID International Symposium, 2018, 49, 339-342.	0.1	3
93	Enhanced gate stack stability in GaN transistors with gate dielectric of bilayer SiNx by low pressure chemical vapor deposition. Applied Physics Letters, 2018, 113, .	1.5	6
94	High-Performance AlGaN/GaN/Si Power MOSHEMTs With ZrO₂ Gate Dielectric. IEEE Transactions on Electron Devices, 2018, 65, 5337-5342.	1.6	22
95	GaAs Solar Cells on Nanopatterned Si Substrates. IEEE Journal of Photovoltaics, 2018, 8, 1635-1640.	1.5	23
96	Epitaxial growth of high quality InP on Si substrates: The role of InAs/InP quantum dots as effective dislocation filters. Journal of Applied Physics, 2018, 123, .	1.1	24
97	Room-temperature electrically-pumped 15 Î¼m InGaAs/InAlGaAs laser monolithically grown on on-axis (001) Si. Optics Express, 2018, 26, 14514.	1.7	35
98	Monolithic integration of III-nitride voltage-controlled light emitters with dual-wavelength photodiodes by selective-area epitaxy. Optics Letters, 2018, 43, 3401.	1.7	42
99	A power inductor integration technology using a silicon interposer for DC-DC converter applications. , 2018, , .		4
100	Experimental characterization of the fully integrated Si-GaN cascoded FET. , 2018, , .		3
101	Room-temperature InP/InGaAs nano-ridge lasers grown on Si and emitting at telecom bands. Optica, 2018, 5, 918.	4.8	40
102	Self-organized InAs/InAlGaAs quantum dots as dislocation filters for InP films on (001) Si. Journal of Crystal Growth, 2017, 464, 28-32.	0.7	31
103	Continuous-Wave Optically Pumped 1.55 Î¼m InAs/InAlGaAs Quantum Dot Microdisk Lasers Epitaxially Grown on Silicon. ACS Photonics, 2017, 4, 204-210.	3.2	56
104	Fully- and Quasi-Vertical GaN-on-Si p-i-n Diodes: High Performance and Comprehensive Comparison. IEEE Transactions on Electron Devices, 2017, 64, 809-815.	1.6	45
105	Investigation of <italic>In Situ</italic> SiN as Gate Dielectric and Surface Passivation for GaN MISHEMTs. IEEE Transactions on Electron Devices, 2017, 64, 832-839.	1.6	80
106	Study of Interface Traps in AlGaN/GaN MISHEMTs Using LPCVD SiN_{<italic>x</italic>} as Gate Dielectric. IEEE Transactions on Electron Devices, 2017, 64, 824-831.	1.6	58
107	A Novel Siâ€“GaN Monolithic Integration Technology for a High-Voltage Cascoded Diode. IEEE Electron Device Letters, 2017, 38, 501-504.	2.2	13
108	1.55â€‰Î¼m room-temperature lasing from subwavelength quantum-dot microdisks directly grown on (001) Si. Applied Physics Letters, 2017, 110, .	1.5	50

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109	Switching performance of quasi-vertical GaN-based p-i-n diodes on Si. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600817.	0.8	15
110	25â€5: Distinguished Student Paper: Fullyâ€Integrated Active Matrix Programmable UV and Blue Microâ€LED Display Systemâ€onâ€Panel (SoP). Digest of Technical Papers SID International Symposium, 2017, 48, 357-361.	0.1	10
111	Fully-integrated active matrix programmable UV and blue micro-LED display system-on-panel (SoP). Journal of the Society for Information Display, 2017, 25, 240-248.	0.8	56
112	InAs quantum dot micro-disk lasers grown on (001) Si emitting at communication wavelengths. , 2017, , .		1
113	High Performance Monolithically Integrated GaN Driving VMOSFET on LED. IEEE Electron Device Letters, 2017, 38, 752-755.	2.2	18
114	Fin-Array Tunneling Trigger With Tunable Hysteresis on (001) Silicon Substrate. IEEE Electron Device Letters, 2017, 38, 556-559.	2.2	8
115	Epitaxial growth of GaSb on V-grooved Si (001) substrates with an ultrathin GaAs stress relaxing layer. Applied Physics Letters, 2017, 111, .	1.5	23
116	Low-Flicker Lighting From High-Voltage LEDs Driven by a Single Converter-Free Driver. IEEE Photonics Technology Letters, 2017, 29, 1675-1678.	1.3	3
117	Switching characteristics of monolithically integrated Si-GaN cascoded rectifiers. , 2017, , .		3
118	Continuous-wave lasing from InP/InGaAs nanoridges at telecommunication wavelengths. Applied Physics Letters, 2017, 111, 212101.	1.5	23
119	Epitaxial growth of highly mismatched III-V materials on (001) silicon for electronics and optoelectronics. Progress in Crystal Growth and Characterization of Materials, 2017, 63, 105-120.	1.8	108
120	Room Temperature 1.55 pm Lasing of Sub-wavelength Quantum-dot Lasers Epitaxially Grown on (001) Silicon. , 2017, , .		0
121	Tristate Memory Cells Using Double-Peaked Fin-Array IIIâ€“V Tunnel Diodes Monolithically Grown on (001) Silicon Substrates. IEEE Transactions on Electron Devices, 2017, 64, 4078-4083.	1.6	7
122	Fully-integrated AMLED micro display system with a hybrid voltage regulator. , 2017, , .		10
123	GaAs Solar Cells on V-Grooved Silicon via Selective Area Growth. , 2017, , .		1
124	Electrically pumped continuous wave quantum dot lasers epitaxially grown on patterned, on-axis (001) Si. Optics Express, 2017, 25, 3927.	1.7	103
125	O-band electrically injected quantum dot micro-ring lasers on on-axis (001) GaP/Si and V-groove Si. Optics Express, 2017, 25, 26853.	1.7	53
126	Monolithically integrated InAs/InGaAs quantum dot photodetectors on silicon substrates. Optics Express, 2017, 25, 27715.	1.7	71

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127	Parametric study of high-performance 155 Î¼m InAs quantum dot microdisk lasers on Si. Optics Express, 2017, 25, 31281.	1.7	14
128	13â€‰â€‰Î¼m submilliamp threshold quantum dot micro-lasers on Si. Optica, 2017, 4, 940.	4.8	142
129	155â€‰â€‰Î¼m band low-threshold, continuous-wave lasing from InAs/InAlGaAs quantum dot microdisks. Optics Letters, 2017, 42, 679.	1.7	24
130	13-Î¼m InAs quantum-dot micro-disk lasers on V-groove patterned and unpatterned (001) silicon. Optics Express, 2016, 24, 21038.	1.7	37
131	Optically pumped 13â€‰â€‰Î¼m room-temperature InAs quantum-dot micro-disk lasers directly grown on (001) silicon. Optics Letters, 2016, 41, 1664.	1.7	101
132	Optimization of electrode structure for flipâ€chip HVLED via twoâ€level metallization. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1199-1203.	0.8	6
133	Off-state leakage current reduction in AlGaN/GaN high electron mobility transistors by combining surface treatment and post-gate annealing. Semiconductor Science and Technology, 2016, 31, 055019.	1.0	29
134	Highly ordered horizontal indium gallium arsenide/indium phosphide multi-quantum-well in wire structure on (001) silicon substrates. Journal of Applied Physics, 2016, 120, .	1.1	19
135	Monolithic integration of enhancement-mode vertical driving transistorson a standard InGaN/GaN light emitting diode structure. Applied Physics Letters, 2016, 109, .	1.5	28
136	Temperature characteristics of epitaxially grown InAs quantum dot micro-disk lasers on silicon for on-chip light sources. Applied Physics Letters, 2016, 109, .	1.5	31
137	High voltage low current collapse AlGaN/GaN MISHEMTs with in-situ SiN gate dielectric. , 2016, , .		0
138	Sub-wavelength InAs quantum dot micro-disk lasers epitaxially grown on exact Si (001) substrates. Applied Physics Letters, 2016, 108, .	1.5	58
139	Fabrication and improved performance of AlGaN/GaN HEMTs with regrown ohmic contacts and passivation-first process. , 2016, , .		2
140	Monolithically integrated GaN-based HEMT-LED and InGaN/GaN photodiodes for on-chip optical interconnects. , 2016, , .		0
141	Fully Vertical GaN p-i-n Diodes Using GaN-on-Si Epilayers. IEEE Electron Device Letters, 2016, 37, 636-639.	2.2	86
142	Monolithic Integration of Tunnel Diode Based Inverters on Exact (001) Si Substrates. IEEE Electron Device Letters, 2016, , 1-1.	2.2	4
143	Design and Characterization of Active Matrix LED Microdisplays With Embedded Visible Light Communication Transmitter. Journal of Lightwave Technology, 2016, 34, 3449-3457.	2.7	55
144	Optimization of a Common Buffer Platform for Monolithic Integration of InGaN/GaN Light-Emitting Diodes and AlGaN/GaN High-Electron-Mobility Transistors. Journal of Electronic Materials, 2016, 45, 2092-2101.	1.0	7

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145	Coalescence of planar GaAs nanowires into strain-free three-dimensional crystals on exact (001) silicon. Journal of Crystal Growth, 2016, 454, 19-24.	0.7	8
146	Investigation of Photon-Generated Leakage Current for High-Performance Active Matrix Micro-LED Displays. IEEE Transactions on Electron Devices, 2016, 63, 4832-4838.	1.6	46
147	Homogeneous and heterogeneous integration of GaN-based light emitting diodes and driving transistors. , 2016, , .		1
148	Breakdown Ruggedness of Quasi-Vertical GaN-Based p-i-n Diodes on Si Substrates. IEEE Electron Device Letters, 2016, 37, 1158-1161.	2.2	30
149	Growing InGaAs quasi-quantum wires inside semi-rhombic shaped planar InP nanowires on exact (001) silicon. Applied Physics Letters, 2016, 108, 242105.	1.5	33
150	GaAs-InGaAs-GaAs Fin-Array Tunnel Diodes on (001) Si Substrates With Room-Temperature Peak-to-Valley Current Ratio of 5.4. IEEE Electron Device Letters, 2016, 37, 24-27.	2.2	22
151	Fabrication and Characterization of High-Voltage LEDs Using Photoresist-Filled-Trench Technique. Journal of Display Technology, 2016, 12, 397-401.	1.3	6
152	Low-Leakage High-Breakdown Laterally Integrated HEMT-LED via n-GaN Electrode. IEEE Photonics Technology Letters, 2016, 28, 1130-1133.	1.3	39
153	Off-state drain leakage reduction by post metallization annealing for Al₂ O₃ /GaN/AlGaN/GaN MOSHEMTs on Si. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 868-872.	0.8	7
154	Vertical LEDs on Rigid and Flexible Substrates Using GaN-on-Si Epilayers and Au-Free Bonding. IEEE Transactions on Electron Devices, 2016, 63, 1587-1593.	1.6	17
155	Full-Color Pixelated-Addressable Light Emitting Diode on Transparent Substrate (LEDoTS) Micro-Displays by CoB. Journal of Display Technology, 2016, 12, 742-746.	1.3	47
156	Enhanced optical properties of InAs/InAlGaAs/InP quantum dots grown by metal-organic chemical vapor deposition using a double-cap technique. Journal of Crystal Growth, 2016, 433, 19-23.	0.7	17
157	Fabrication and Characterization of Gate-Last Self-Aligned AlN/GaN MISHEMTs With <italic>In Situ</italic> SiN_{<italic>x</italic>} Gate Dielectric. IEEE Transactions on Electron Devices, 2015, 62, 1862-1869.	1.6	22
158	InAs/GaAs quantum dots on GaAs-on-V-grooved-Si substrate with high optical quality in the 1.3â€‰Î¼m band. Applied Physics Letters, 2015, 107, .	1.5	39
159	Metal-interconnection-free integration of InGaN/GaN light emitting diodes with AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2015, 106, .	1.5	45
160	GaN-based LED micro-displays for wearable applications. Microelectronic Engineering, 2015, 148, 98-103.	1.1	114
161	Growing antiphase-domain-free GaAs thin films out of highly ordered planar nanowire arrays on exact (001) silicon. Applied Physics Letters, 2015, 106, .	1.5	135
162	A low substrate loss, monolithically integrated power inductor for compact LED drivers. , 2015, , .		9

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163	Improved breakdown characteristics of monolithically integrated III-nitride HEMTâ€“LED devices using carbon doping. Journal of Crystal Growth, 2015, 414, 243-247.	0.7	7
164	MOVPE growth of in situ SiNx/AlN/GaN MISHEMTs with low leakage current and high on/off current ratio. Journal of Crystal Growth, 2015, 414, 237-242.	0.7	13
165	1700 Pixels Per Inch (PPI) Passive-Matrix Micro-LED Display Powered by ASIC. , 2014, , .		47
166	III–V-IV integration toward electronics and photonics convergence on a silicon platform. , 2014, , .		0
167	Solid-State Lighting with High Brightness, High Efficiency, and Low Cost. International Journal of Photoenergy, 2014, 2014, 1-3.	1.4	0
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